

EAST - [10726050.wsp:1]

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L1: (112) ((integrated adj circuit) or "IC") and ((non adj fl
L2: (159) ((integrated adj circuit) or "IC") and ((non adj fl
L3: (52) 2 and (terminal and (solder or ball or pad))
L4: (9) 3 and (capacitor and (insulat\$4 or dielectric))
L5: (4) "6686659"
L6: (7) Backward citation search 1
L9: (12) Backward citation search 2
L10: (20) Forward citation search 2
L12: (2) 11 and decoupl\$4
L11: (32) 3 not (4 5 6 7 9 10)

S1: (290) substrate and ((bump or solder or (solder adj ball)
S2: (59) seshan-krishna.in.
S3: (24) ("4141022"|"5605861"|"5770490"|"5882965"|"5937289"|"5
S4: (3) seshan-krishna.in. and ("IC" or (integrated adj circuit
S5: (1) (US-20040108596-5).did.
S6: (1) US-20040108596-A1.DID. and (float\$4 or (non-float\$4))
S7: (24) ("4141022"|"5605861"|"5770490"|"5882965"|"5937289"|"5
S8: (7) ("4273859"|"5808853"|"6094090"|"6175345"|"6222246"|"62

US-PGPUB; USPAT; EPO; WPO; DERWENT; IBM; TDB

Default operator: OR

3 and (capacitor and (insulat\$4 or dielectric))

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	U	1	PT	P	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
1	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20030234660 A1	20031225	10	Direct landing technology for wafer probe	324/765	
2	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20020119583 A1	20020829	23	Selectable decoupling capacitors for integrated circuit and methods of use	438/17	257/E23.079; 257/E23.171
3	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 20020008267 A1	20020124	24	Deep trench semiconductor capacitors having reverse bias diodes for implantable medical devices	257/301	257/106; 257/E21.396;
4	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 6686659 B2	20040203	22	Selectable decoupling capacitors for integrated circuit and methods of use	257/737	257/532; 257/E23.079;
5	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 6484054 B2	20021119	23	Deep trench semiconductor capacitors having reverse bias diodes for implantable medical devices	607/2	257/E21.396; 257/E27.048;
6	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 6452514 B1	20020917	17	Capacitive sensor and array	341/33	178/18.06; 341/22
7	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 6040608 A	20000321	9	Field-effect transistor for one-time programmable nonvolatile memory element	257/390	257/356; 257/391;
8	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	<input type="checkbox"/>	US 5358514 A	19941025	17	Implantable microdevice with self-attaching electrodes	607/61	607/118

Ready